

# Ilya A Eliseyev

## List of Publications by Year in descending order

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48  
papers

299  
citations

933264

10  
h-index

996849

15  
g-index

48  
all docs

48  
docs citations

48  
times ranked

284  
citing authors

#	ARTICLE	IF	CITATIONS
1	Study of the crystal and electronic structure of graphene films grown on 6H-SiC (0001). Semiconductors, 2017, 51, 1072-1080.	0.2	44
2	Multiwall MoS <sub>2</sub> tubes as optical resonators. Applied Physics Letters, 2018, 113, .	1.5	30
3	Graphene on SiC Substrate as Biosensor: Theoretical Background, Preparation, and Characterization. Materials, 2021, 14, 590.	1.3	15
4	Growth of III-N/graphene heterostructures in single vapor phase epitaxial process. Journal of Crystal Growth, 2018, 504, 1-6.	0.7	14
5	Phonons in Short-Period GaN/AlN Superlattices: Group-Theoretical Analysis, Ab initio Calculations, and Raman Spectra. Nanomaterials, 2021, 11, 286.	1.9	14
6	Comparative characterization of graphene grown by chemical vapor deposition, transferred to nonconductive substrate, and subjected to Ar ion bombardment using X-ray photoelectron and Raman spectroscopies. Diamond and Related Materials, 2017, 76, 14-20.	1.8	12
7	Investigation of epitaxial graphene via Raman spectroscopy: Origins of phonon mode asymmetries and line width deviations. Carbon, 2020, 170, 666-676.	5.4	12
8	Intercalation of Iron Atoms under Graphene Formed on Silicon Carbide. Physics of the Solid State, 2018, 60, 1439-1446.	0.2	11
9	Surface Nanostructuring during Selective Area Epitaxy of Heterostructures with InGaAs QWs in the Ultra-Wide Windows. Nanomaterials, 2021, 11, 11.	1.9	11
10	Localization and transient emission properties in InGaN/GaN quantum wells of different polarities within core-shell nanorods. Nanoscale, 2019, 11, 193-199.	2.8	10
11	Radiation Defects in Heterostructures 3C-SiC/4H-SiC. Crystals, 2019, 9, 115.	1.0	10
12	State-of-the-art and prospects for intense red radiation from core-shell InGaN/GaN nanorods. Scientific Reports, 2020, 10, 19048.	1.6	10
13	High Quality Graphene Grown by Sublimation on 4H-SiC (0001). Semiconductors, 2018, 52, 1882-1885.	0.2	9
14	Optical Estimation of the Carrier Concentration and the Value of Strain in Monolayer Graphene Grown on 4H-SiC. Semiconductors, 2019, 53, 1904-1909.	0.2	9
15	Quasi-freestanding graphene on SiC(0001) via cobalt intercalation of zero-layer graphene. Physical Review B, 2021, 104, .	1.1	8
16	MoS <sub>2</sub> flake as a van der Waals homostructure: luminescence properties and optical anisotropy. Nanoscale, 2021, 13, 17566-17575.	2.8	7
17	Complex XPS and Raman Study of Graphene on Copper and Si/SiO <sub>2</sub> ; Subjected to Ar Ion Treatment. Key Engineering Materials, 0, 721, 258-262.	0.4	6
18	Study of properties and development of sensors based on graphene films grown on SiC (0001) by thermal destruction method. Journal of Physics: Conference Series, 2018, 951, 012007.	0.3	6

#	ARTICLE	IF	CITATIONS
19	Temperature activation of indirect exciton in nanostructures based on MoS <sub>2</sub> . Journal of Physics: Conference Series, 2020, 1482, 012038.	0.3	6
20	Surface morphology control of the SiC (0001) substrate during the graphene growth. Fullerenes Nanotubes and Carbon Nanostructures, 2020, 28, 281-285.	1.0	5
21	The Effect of Interface Diffusion on Raman Spectra of Wurtzite Short-Period GaN/AlN Superlattices. Nanomaterials, 2021, 11, 2396.	1.9	5
22	State memory in solution gated epitaxial graphene. Applied Surface Science, 2018, 444, 36-41.	3.1	4
23	Photoluminescence Kinetics of Dark and Bright Excitons in Atomically Thin MoS <sub>2</sub> . Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100263.	1.2	4
24	Transport properties of graphene films grown by thermodestruction of SiC (0001) surface in argon medium. Technical Physics Letters, 2017, 43, 849-852.	0.2	3
25	Comparative Investigation of the Graphene-on-Silicon Carbide and CVD Graphene as a Basis for Biosensor Application. Key Engineering Materials, 0, 799, 185-190.	0.4	3
26	Phonons in short-period (GaN) <sub>m</sub> (AlN) <sub>n</sub> superlattices: ab initio calculations and group-theoretical analysis of modes and their genesis. Journal of Physics: Conference Series, 2019, 1400, 066016.	0.3	3
27	Investigation of the Hydrogen Etching Effect of the SiC Surface on the Formation of Graphene Films. Technical Physics, 2019, 64, 1843-1849.	0.2	3
28	Modification of the Electronic Structure of Quasi-Free-Standing Graphene by the Adsorption and Intercalation of Mn Atoms. Journal of Experimental and Theoretical Physics, 2021, 132, 906-916.	0.2	3
29	Graphene on silicon carbide as a basis for gas- and biosensor applications. Nanosystems: Physics, Chemistry, Mathematics, 2018, , 95-97.	0.2	3
30	Raman scattering and low-frequency noise in epitaxial graphene chips. Journal of Physics: Conference Series, 2020, 1697, 012130.	0.3	3
31	A Blueprint for the Synthesis and Characterization of Thiolated Graphene. Nanomaterials, 2022, 12, 45.	1.9	3
32	Detection of lysine molecular ions in solution gated field effect transistors based on unmodified graphene. Journal of Applied Physics, 2020, 128, 215302.	1.1	2
33	Comparison of graphene films grown on 6<i>H</i>-SiC and 4<i>H</i>-SiC substrates. Fullerenes Nanotubes and Carbon Nanostructures, 2020, 28, 321-324.	1.0	2
34	Photoluminescence enhancement in multilayered MoSe <sub>2</sub> nanostructures obtained by local anodic oxidation. 2D Materials, 2022, 9, 015010.	2.0	2
35	Raman spectra of interface phonons in long-period AlN/GaN superlattices as a tool for determination of the structure period. Journal of Physics: Conference Series, 2019, 1400, 066003.	0.3	1
36	Boson Peak Related to Ga Nanoclusters in AlGaIn Layers Grown by Plasma-Assisted Molecular Beam Epitaxy at Ga-Rich Conditions. Semiconductors, 2019, 53, 1479-1488.	0.2	1

#	ARTICLE	IF	CITATIONS
37	Local anodic oxidation as a method of fabrication optoelectronic devices based on thin TMDC layers. AIP Conference Proceedings, 2020, , .	0.3	1
38	Transformation of the buffer layer grown on 4H-SiC to single-layer graphene by <i>ex situ</i> hydrogen intercalation. Fullerenes Nanotubes and Carbon Nanostructures, 2020, 28, 316-320.	1.0	1
39	Raman and AFM studies of epitaxial graphene intended for manufacturing of transistors. Journal of Physics: Conference Series, 2020, 1695, 012018.	0.3	1
40	Raman spectroscopy estimation of the carrier concentration and the value of strain in monolayer graphene films grown on 4H-SiC. Journal of Physics: Conference Series, 2019, 1400, 055037.	0.3	1
41	Analysis of the sharpness of interfaces in short-period GaN/AlN superlattices using Raman spectroscopy data. Journal of Physics: Conference Series, 2021, 2103, 012147.	0.3	1
42	Raman spectra of GaSe epitaxial layers grown on GaAs substrates and group-theoretical analysis of their vibrational modes. Journal of Physics: Conference Series, 2019, 1400, 055007.	0.3	0
43	Structural and Dynamical Properties of Short-Period GaN/AlN Superlattices: Experiment and Theory. Semiconductors, 2020, 54, 1706-1709.	0.2	0
44	A Study of the Photoresponse in Graphene Produced by Chemical Vapor Deposition. Semiconductors, 2020, 54, 991-998.	0.2	0
45	Graphene Quality Assessment Using an Entropy Approach of SEM Images. Materials Science Forum, 0, 1004, 525-530.	0.3	0
46	Raman Studies of Graphene Films Grown on 4H-SiC Subjected to Deposition of Ni. Semiconductors, 2020, 54, 1674-1677.	0.2	0
47	Comparative Study of Conventional and Quasi-Freestanding Epitaxial Graphenes Grown on 4H-SiC Substrate. Semiconductors, 2020, 54, 1657-1660.	0.2	0
48	Investigation of electrolysis-related modification of graphene films in biosensors. Journal of Physics: Conference Series, 2021, 2103, 012103.	0.3	0